

Abstract

An interleave control device using a nonvolatile ferroelectric memory is disclosed. More specifically, a
5 memory interleave structure using a nonvolatile ferroelectric register configured to individually control interleaves of banks is disclosed. In an embodiment of the present invention, interleaves of each bank can be individually controlled using a single nonvolatile
10 ferroelectric memory chip, a multi-bank nonvolatile ferroelectric memory chip or a multi-bank interleave nonvolatile ferroelectric memory chip.